HW-8

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A) Xichen Li: I did HW8 independently.

Chapter-12 P3:

Plot the density of states as a function of Energy for a GaAs wire with a 6nm * 6nm square cross-section. In plotting the DOS, choose a point located at the center of the square cross-section. Show the DOS contribution due to each sub-band and the total DOS. Include at least the three lowest sub-bands in the conduction band and the three highest sub-bands in the valence band. Assume that the effective mass of electrons and holes are $0.067m_o$ and $0.47m_o$, respectively.

Answer

In a 1-D nanowire nanostructure, the DOS in the conduction band is:

$$DOS_{c}(x, y, z, E) = \frac{4}{L_{1}L_{2}} \frac{1}{\pi\hbar} \sum_{l,m} sin^{2} (\frac{l\pi}{L_{1}} x) sin^{2} (\frac{m\pi}{L_{2}} y) \sqrt{\frac{m_{c}}{2(E - E_{c} - \epsilon_{l,m})}} u(E - E_{c} - \epsilon_{l,m})$$

where $\epsilon_{l,m} = \frac{\hbar^2}{2m_c} (\frac{l\pi}{L_1})^2 + \frac{\hbar^2}{2m_c} (\frac{m\pi}{L_2})^2$. Here we consider the three lowest sub-band in the conduction band where (l,m) = (1,1), (1,2), (2,1), (1,3), (3,1), (2,2), (3,3).

Similar to the derviation for DOS in the conduction band, the DOS in the valence band is:

$$DOS_{v}(x, y, z, E) = \frac{4}{L_{1}L_{2}} \frac{1}{\pi \hbar} \sum_{l', m'} sin^{2} \left(\frac{l'\pi}{L_{1}}x\right) sin^{2} \left(\frac{m'\pi}{L_{2}}y\right) \sqrt{\frac{m_{c}}{2(E_{v} - \epsilon_{l', m'} - E)}} u(E_{v} - \epsilon_{l', m'} - E)$$

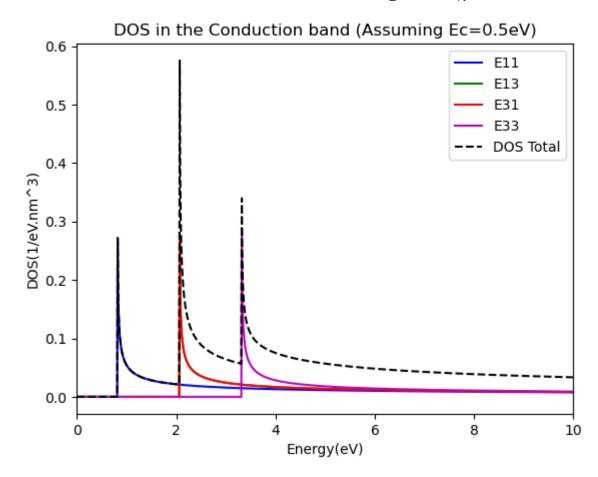
The question is ask to choose a point at the center of the square cross section, thus $x = y = \frac{L}{2} = 3nm$.

The density of states in conduction band and valence band as a function of energy are plotted using the code below.

```
In [3]: import numpy as np
        %matplotlib inline
        import matplotlib.pyplot as plt
        eta = 6.63e-34/2/np.pi #Reduced Plank constant in eV.s
        q = 1.6e-19
        L1=6e-9
        L2=L1
        x=L1/2
        mo = 9.11e-31
        mc = 0.067*mo
        mv = 0.47*mo
        Ec = 0.5*q
        BG=1.42*q #bandgap of the bulk semiconductor
        Eend=10*q
        dE=0.1e-1*q
        E=np.arange(0, Eend, dE)
        def u(X):
            U=[]
            for x in X:
                if x >0:
                  result = 1
                else:
                  result = 0
                U=np.append(U,result)
            return U
        def SQRT(X):
            U=[]
            for x in X:
                if x >0:
                  result = np.sqrt(x)
                else:
                  result = 0
                U=np.append(U,result)
            return U
        C1=4/(L1*L2)*1/(np.pi*eta)
        #Density of State in the conduction band
        eps11=eta**2/(2*mc)*(1*np.pi/L1)**2+eta**2/(2*mc)*(1*np.pi/L2)**2
        DOSc11=C1*((np.sin(1*np.pi*x/L1))**2)*((np.sin(1*np.pi*x/L1))**2)*SQRT(mc/(2*(E-Ec-eps11)))*u(E-Ec-eps11))
```

```
eps12=eta**2/(2*mc)*(1*np.pi/L1)**2+eta**2/(2*mc)*(2*np.pi/L2)**2
DOSc12 = C1*((np.sin(1*np.pi*x/L1))**2)*((np.sin(2*np.pi*x/L1))**2)*SQRT(mc/(2*(E-Ec-eps12)))*u(E-Ec-eps12))
eps21=eta**2/(2*mc)*(2*np.pi/L1)**2+eta**2/(2*mc)*(1*np.pi/L2)**2
DOSc21=C1*((np.sin(2*np.pi*x/L1))**2)*((np.sin(1*np.pi*x/L1))**2)*SQRT(mc/(2*(E-Ec-eps21)))*u(E-Ec-eps21)
eps22=eta**2/(2*mc)*(2*np.pi/L1)**2+eta**2/(2*mc)*(2*np.pi/L2)**2
DOSc22 = C1*((np.sin(2*np.pi*x/L1))**2)*((np.sin(2*np.pi*x/L1))**2)*SQRT(mc/(2*(E-Ec-eps22)))*u(E-Ec-eps22)
eps13=eta**2/(2*mc)*(1*np.pi/L1)**2+eta**2/(2*mc)*(3*np.pi/L2)**2
DOSc13=C1*((np.sin(1*np.pi*x/L1))**2)*((np.sin(3*np.pi*x/L1))**2)*SQRT(mc/(2*(E-Ec-eps13)))*u(E-Ec-eps13))
eps31=eta**2/(2*mc)*(3*np.pi/L1)**2+eta**2/(2*mc)*(1*np.pi/L2)**2
DOSc31=C1*((np.sin(3*np.pi*x/L1))**2)*((np.sin(1*np.pi*x/L1))**2)*SQRT(mc/(2*(E-Ec-eps31)))*u(E-Ec-eps31))
eps33=eta**2/(2*mc)*(3*np.pi/L1)**2+eta**2/(2*mc)*(3*np.pi/L2)**2
DOSc33=C1*((np.sin(3*np.pi*x/L1))**2)*((np.sin(3*np.pi*x/L1))**2)*SQRT(mc/(2*(E-Ec-eps33)))*u(E-Ec-eps33))
DOSc=DOSc11+DOSc12+DOSc21+DOSc22+DOSc13+DOSc31+DOSc33
plt.figure()
plt.plot(E/q, DOSc11*q/1e27, color='b', ls='-')
#plt.plot(E/q, DOSc12*q/1e27, color='b', ls='-')
#plt.plot(E/q, DOSc21*q/1e27, color='b', ls='-')
#plt.plot(E/q, DOSc22*q/1e27, color='b', ls='-')
plt.plot(E/q, DOSc13*q/1e27, color='g', ls='-')
plt.plot(E/q, DOSc31*q/1e27, color='r', ls='-')
plt.plot(E/q, DOSc33*q/1e27, color='m', ls='-')
plt.plot(E/q, DOSc*q/1e27, color='k', ls='--')
plt.legend(['E11', 'E13', 'E31', 'E33', 'DOS Total'])
plt.title('DOS in the Conduction band (Assuming Ec=0.5eV)')
plt.xlabel('Energy(eV)')
plt.ylabel('DOS(1/eV.nm^3)')
plt.xlim(0, Eend/q)
```

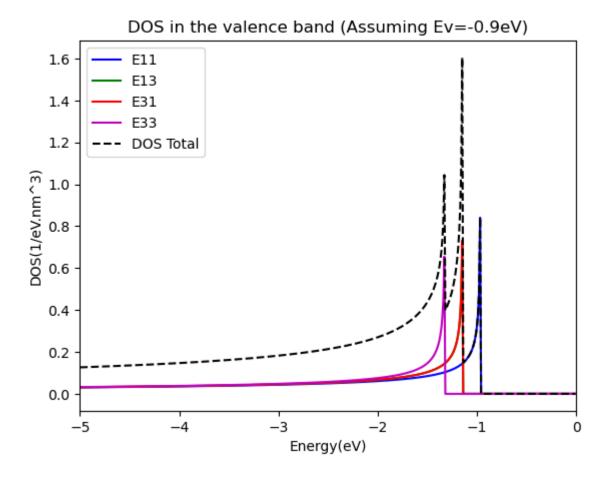
Out[3]: (0.0, 10.0)



```
In [4]: Ev=Ec-BG
        Estartv=-5*q
        dE=0.1e-1*q
        E1=np.arange(Estartv,0,dE)
        #Density of State in the conduction band
        epsv11=eta**2/(2*mv)*(1*np.pi/L1)**2+eta**2/(2*mv)*(1*np.pi/L2)**2
        DOSv11=C1*((np.sin(1*np.pi*x/L1))**2)*((np.sin(1*np.pi*x/L1))**2)*SQRT(mv/(2*(Ev-epsv11-E1)))*u(Ev-epsv11-E1))
        epsv12=eta**2/(2*mv)*(1*np.pi/L1)**2+eta**2/(2*mv)*(2*np.pi/L2)**2
        DOSv12 = C1*((np.sin(1*np.pi*x/L1))**2)*((np.sin(2*np.pi*x/L1))**2)*SQRT(mv/(2*(Ev-epsv12-E1)))*u(Ev-epsv12-E1))
        epsv21=eta**2/(2*mv)*(2*np.pi/L1)**2+eta**2/(2*mv)*(1*np.pi/L2)**2
        DOSv21 = C1*((np.sin(2*np.pi*x/L1))**2)*((np.sin(1*np.pi*x/L1))**2)*SQRT(mv/(2*(Ev-epsv21-E1)))*u(Ev-epsv21-E1))
        epsv22=eta**2/(2*mv)*(2*np.pi/L1)**2+eta**2/(2*mv)*(2*np.pi/L2)**2
        DOSv22 = C1*((np.sin(2*np.pi*x/L1))**2)*((np.sin(2*np.pi*x/L1))**2)*SQRT(mv/(2*(Ev-epsv22-E1)))*u(Ev-epsv22-E1))
        epsv13=eta**2/(2*mv)*(1*np.pi/L1)**2+eta**2/(2*mv)*(3*np.pi/L2)**2
        DOSv13 = C1*((np.sin(1*np.pi*x/L1))**2)*((np.sin(3*np.pi*x/L1))**2)*SQRT(mv/(2*(Ev-epsv13-E1)))*u(Ev-epsv13-E1)
        epsv31=eta**2/(2*mv)*(3*np.pi/L1)**2+eta**2/(2*mv)*(1*np.pi/L2)**2
        DOSv31=C1*((np.sin(3*np.pi*x/L1))**2)*((np.sin(1*np.pi*x/L1))**2)*SQRT(mv/(2*(Ev-epsv31-E1)))*u(Ev-epsv31-E1))
        epsv33=eta**2/(2*mv)*(3*np.pi/L1)**2+eta**2/(2*mv)*(3*np.pi/L2)**2
        DOSv33 = C1*((np.sin(3*np.pi*x/L1))**2)*((np.sin(3*np.pi*x/L1))**2)*SQRT(mv/(2*(Ev-epsv33-E1)))*u(Ev-epsv33-E1))
        DOSv=DOSv11+DOSv12+DOSv21+DOSv22+DOSv13+DOSv31+DOSv33
        plt.figure()
        plt.plot(E1/q, DOSv11*q/1e27, color='b', ls='-')
        plt.plot(E1/q, DOSv13*q/1e27, color='g', ls='-')
        plt.plot(E1/q, DOSv31*q/1e27, color='r', ls='-')
        plt.plot(E1/q, DOSv33*q/1e27, color='m', ls='-')
        plt.plot(E1/q, DOSv*q/1e27, color='k', ls='--')
        plt.legend(['E11', 'E13', 'E31', 'E33', 'DOS Total'])
        plt.title('DOS in the valence band (Assuming Ev=-0.9eV)')
        plt.xlabel('Energy(eV)')
        plt.ylabel('DOS(1/eV.nm^3)')
```

plt.xlim(Estartv/q, 0)

Out[4]: (-5.0, 0.0)



Chapter-13 P1:

Calculate the electron and hole density in a 1-D nanowire with a bandgap of 1eV. The effective mass of the conduction and valence bands is the free electron mass m_o . By assuming that there is only a single subband in the nanowire's conduction and valence bands, (a) write down the expression for calculating the electron and hole densities and simplify it as much as possible, and (b) calculate a numerical value for the electron and hole densities by assuming that the Fermi energy is 200meV below the nanowire's conduction band.

Answer

Part (a)

The electron density in the conduction band is:

$$n_e(r) = \int_{E_{c,min}}^{E_{c,max}} DOS_c(r, E) f(E) dE$$

In a 1-D nanowire nanostructure, the DOS in the conduction band is:

$$DOS_{c}(x, y, z, E) = \frac{4}{L_{1}L_{2}} \frac{1}{\pi \hbar} \sum_{l,m} sin^{2} (\frac{l\pi}{L_{1}} x) sin^{2} (\frac{m\pi}{L_{2}} y) \sqrt{\frac{m_{c}}{2(E - E_{c} - \epsilon_{l,m})}} u(E - E_{c} - \epsilon_{l,m})$$

where $\epsilon_{l,m} = \frac{\hbar^2}{2m_c} (\frac{l\pi}{L_1})^2 + \frac{\hbar^2}{2m_c} (\frac{m\pi}{L_2})^2$. By assuming that there is only a single subband in the nanowire's conduction bands according to the problem description, we assume l = m = 1. Then the DOS in the conduction band is:

$$DOS_{c}(x, y, z, E) = \frac{4}{L_{1}L_{2}} \frac{1}{\pi \hbar} sin^{2} (\frac{\pi}{L_{1}} x) sin^{2} (\frac{\pi}{L_{2}} y) \sqrt{\frac{m_{c}}{2(E - E_{c} - \epsilon_{1,1})}} u(E - E_{c} - \epsilon_{1,1})$$

where $\epsilon_{1,1} = \frac{\hbar^2}{2m_c} [(\frac{\pi}{L_1})^2 + (\frac{\pi}{L_2})^2].$

Defining $A = \frac{4}{L_1 L_2} \frac{1}{\pi \hbar} \sqrt{m_c}$, then the electron density is:

$$n_{e}(x,y) = A sin^{2}(\frac{\pi}{L_{1}}x) sin^{2}(\frac{\pi}{L_{2}}y) \int_{E_{c,min}}^{E_{c,max}} \sqrt{\frac{1}{2(E - E_{c} - \epsilon_{1,1})}} u(E - E_{c} - \epsilon_{1,1}) f(E) dE$$

Defining $E_{c,1} = E_c + \epsilon_{1,1}$,

$$n_e(x, y) = A sin^2(\frac{\pi}{L_1} x) sin^2(\frac{\pi}{L_2} y) \int_{E_{c,1}}^{\infty} \sqrt{\frac{1}{2(E - E_{c,1})}} f(E) dE$$

where $f(E) = \frac{1}{1+e^{\frac{E-E_F}{k_BT}}}$, then $n_e(x,y)$ becomes:

$$n_e(x,y) = A sin^2(\frac{\pi}{L_1}x) sin^2(\frac{\pi}{L_2}y) \int_{E_{c,1}}^{\infty} \sqrt{\frac{1}{2(E - E_{c,1})}} \frac{1}{1 + e^{\frac{E - E_F}{k_B T}}} dE$$

Change of variables: $\eta = \frac{E - E_{c,1}}{k_B T}$ and $\eta_{C1} = \frac{E_F - E_{c,1}}{k_B T}$, then $n_e(x,y)$ becomes:

$$n_e(x,y) = A \sin^2(\frac{\pi}{L_1} x) \sin^2(\frac{\pi}{L_2} y) (\frac{1}{2} k_B T)^{1/2} \int_0^\infty \eta^{-\frac{1}{2}} \frac{1}{(1 + e^{\eta - \eta_{C1}})} d\eta$$

Similar to the lecture note, when $\eta - \eta_{C1} > 3$, $n_e(x, y)$ can be written as:

$$n_{e}(x, y) = A sin^{2} \left(\frac{\pi}{L_{1}}x\right) sin^{2} \left(\frac{\pi}{L_{2}}y\right) \left(\frac{1}{2}k_{B}T\right)^{1/2} \int_{0}^{\infty} \eta^{-\frac{1}{2}} e^{-(\eta - \eta_{C1})} d\eta$$

$$n_{e}(x, y) = A sin^{2} \left(\frac{\pi}{L_{1}}x\right) sin^{2} \left(\frac{\pi}{L_{2}}y\right) \left(\frac{1}{2}k_{B}T\right)^{1/2} e^{\eta_{C1}} \int_{0}^{\infty} \eta^{-\frac{1}{2}} e^{-\eta} d\eta$$

Change of variables again to solve the integral $u = \eta^{\frac{1}{2}}$:

$$n_e(x,y) = A \sin^2(\frac{\pi}{L_1} x) \sin^2(\frac{\pi}{L_2} y) (\frac{1}{2} k_B T)^{1/2} e^{\eta_{C1}} \int_0^\infty 2e^{-u^2} du$$

The Gauss error function has a form of $erf(x)=\frac{2}{\sqrt{\pi}}\int_0^x e^{-t^2}dt$, then $n_e(x,y)$ becomes

$$n_e(x, y) = A sin^2(\frac{\pi}{L_1} x) sin^2(\frac{\pi}{L_2} y) (\frac{1}{2} k_B T)^{1/2} e^{\eta_{C1}} 2 \frac{\sqrt{\pi}}{2} erf(\infty)$$

Since $er f(\infty) = 1$

$$n_e(x, y) = A sin^2 (\frac{\pi}{L_1} x) sin^2 (\frac{\pi}{L_2} y) (\frac{1}{2} k_B T)^{1/2} e^{\eta_{C1}} \sqrt{\pi}$$

The final expression of $n_e(x, y)$ is

$$n_e(x,y) = \frac{4}{L_1 L_2} sin^2 \left(\frac{\pi}{L_1} x\right) sin^2 \left(\frac{\pi}{L_2} y\right) \frac{1}{\pi \hbar} \sqrt{m_c} \left(\frac{1}{2} k_B T\right)^{1/2} e^{\frac{E_F - E_c - \frac{\hbar^2}{2m_c} \left(\frac{\pi}{L_1}\right)^2 - \frac{\hbar^2}{2m_c} \left(\frac{\pi}{L_2}\right)^2}{k_B T}} \sqrt{\pi}$$

Similar to the electron density in the conduction band, the hole density in the valence band is :

$$n_h(r) = \int_{E_{v,min}}^{E_{v,max}} DOS_c(r, E)[1 - f(E)]dE$$

After performing some simplifications and use $B=rac{4}{L_1L_2}rac{1}{\pi\hbar}\sqrt{m_v}$, we can get:

$$n_h(x,y) = B sin^2(\frac{\pi}{L_1}x) sin^2(\frac{\pi}{L_2}y) \int_{-\infty}^{E_{v,1}} \sqrt{\frac{1}{2(E_{v,1} - E)}} [1 - f(E)] dE$$

where $E_{v,1}=E_v-\epsilon_{1,1}$, and again $\epsilon_{1,1}=\frac{\hbar^2}{2m_v}[(\frac{\pi}{L_1})^2+(\frac{\pi}{L_2})^2]$.

$$n_h(x,y) = B sin^2 \left(\frac{\pi}{L_1} x\right) sin^2 \left(\frac{\pi}{L_2} y\right) \int_{-\infty}^{E_{v,1}} \sqrt{\frac{1}{2(E_{v,1} - E)}} \left[1 - \frac{1}{1 + e^{\frac{E - E_F}{k_B T}}}\right] dE$$

Change of variables: $\eta = \frac{E_{v,1}-E}{k_BT}$ and $\eta_{v1} = \frac{E_F-E_{v,1}}{k_BT}$, then $n_h(x,y)$ becomes:

$$n_h(x,y) = \frac{4}{L_1 L_2} \frac{1}{\pi \hbar} \sqrt{m_v} sin^2 (\frac{\pi}{L_1} x) sin^2 (\frac{\pi}{L_2} y) (\frac{1}{2} k_B T)^{\frac{1}{2}} \int_0^\infty \eta^{-\frac{1}{2}} [\frac{1}{1 + e^{-\eta - \eta_{v1}}} - 1] d\eta$$

Part(b)

Becasue the bandgap of this nanowire is 1eV and the Fermi energy is 200meV below the nanowire's conduction band, so we have:

$$E_F - E_{c,1} = E_F - \left[E_c + \frac{\hbar^2}{2m_c} \left(\frac{\pi}{L_1}\right)^2 + \frac{\hbar^2}{2m_c} \left(\frac{\pi}{L_2}\right)^2\right] = -200 \text{meV}$$

$$E_F - E_{v1} = E_F - \left[E_v - \frac{\hbar^2}{2m_e} \left(\frac{\pi}{L_1}\right)^2 - \frac{\hbar^2}{2m_e} \left(\frac{\pi}{L_2}\right)^2\right] = 800 \text{meV}$$

Then the electron density $n_e(x, y)$ at any specific location (x,y) in a naowire is:

$$n_e(x,y) = \frac{4}{L_1 L_2} sin^2 (\frac{\pi}{L_1} x) sin^2 (\frac{\pi}{L_2} y) \frac{1}{\pi \hbar} \sqrt{m_c} (\frac{1}{2} k_B T)^{1/2} e^{\frac{-200 meV}{k_B T}} \sqrt{\pi}$$

By assuming a room temperature T = 298K, $k_BT = 4.11 * 10^{-21}J$

$$n_e(x,y) = \frac{4}{L_1 L_2} sin^2 (\frac{\pi}{L_1} x) sin^2 (\frac{\pi}{L_2} y) \frac{1}{\pi * 6.63 * 10^{-34} / 2/\pi} \sqrt{9.11 * 10^{-31}} (\frac{1}{2} 4.11 * 10^{-21})^{1/2} e^{\frac{-0.2 * 1.6 * 10^{-19}}{4.11 * 10^{-21}}} \sqrt{\pi}$$

$$n_e(x, y) = \frac{1}{L_1 L_2} sin^2(\frac{\pi}{L_1} x) sin^2(\frac{\pi}{L_2} y) * 3.85 * 10^5/m$$

By using $E_F - E_{v1} = 800 meV$, the integral in the expression of the hole density is calculated using Matlab and the resulting $n_h(x, y)$ at any specific location (x,y) in a nanowire is:

$$n_h(x, y) = \frac{1}{L_1 L_2} sin^2 (\frac{\pi}{L_1} x) sin^2 (\frac{\pi}{L_2} y) * (-2.76 * 10^{-5})/m$$

In []:

In []: